



ELECTRONIC TUBE REFERENCE

GM3P

Power - Triode electronic tube

CONSOLIDATED TECHNICAL DATA

1 SECTION

CONSTRUCTION

TRIODE

Russian power triode for low-frequency low-distortion cathode-coupled amplifier service in electronic or RF equipment.

GENERAL CHARACTERISTICS

BASE DESIGNATION	—	BASE PINS	—
NOMINAL HEATER	6.3 V / —	PARALLEL HEATER	— / —
HEATING	Direct	SERIES OPERATION	Not specified
CATHODE ARRANGEMENT	Separate cathodes	SECTION CONSTRUCTION	Similar

SECTION RATINGS

SECTION 1 Triode	
MAXIMUM PLATE VOLTAGE	3000 V
<i>Promoted-field audit performed from English ratings/characteristics; detailed electrical values retained in parameter table.</i>	

The GM-3P triode is used in low-frequency low-distortion cathode-coupled amplifier circuits in stationary RF equipment.

SOURCE OPERATING CONDITIONS

[SOURCE PDF](#)

1968 Electronintorg

Published test conditions and operating points. Values on this page are preserved as reported by this source.

1968 ELECTRONINTORG

Section 1 · Triode

OTHER		
PARAMETER	PUBLISHED VALUE	CONDITION / NOTE
frequency no-distor [1]	3 Hz	The TM-3IM triode is used in low-frequency no-distor- 2 \$58max N OF ELECTRODES
frequency no-distor [2]	2 Hz	The TM-3IM triode is used in low-frequency no-distor- 2 \$58max N OF ELECTRODES
frequency no-distor [3]	58 Hz	The TM-3IM triode is used in low-frequency no-distor- 2 \$58max N OF ELECTRODES
cathode-coupled amplifier circuits in stationary RF g B	5	tion cathode-coupled amplifier circuits in stationary RF g B 05
grid [1]	1	1, 3 - cathode; 2, 4 - grid;
grid [2]	3	1, 3 - cathode; 2, 4 - grid;
grid [3]	2	1, 3 - cathode; 2, 4 - grid;
grid [4]	4	1, 3 - cathode; 2, 4 - grid;
temperature, °C [1]	-10 C	Temnepatypa okpyxaswown cpegpl, °C Ambient temperature, °C —10to +55
temperature, °C [2]	55 C	Temnepatypa okpyxaswown cpegpl, °C Ambient temperature, °C —10to +55
voltages [1]	2 V	2u3ANNMAB Gain coefficient (at anode voltages 2 and
voltages [2]	2 V	2u3ANNMAB Gain coefficient (at anode voltages 2 and
voltage, A [1]	2 A	anoga 2 m 3 kB, Toke aHoga 2 A) Anode current at zero grid voltage, A:
voltage, A [2]	3 A	anoga 2 m 3 kB, Toke aHoga 2 A) Anode current at zero grid voltage, A:

PARAMETER	PUBLISHED VALUE	CONDITION / NOTE
voltage, A [3]	2 A	anoga 2 m 3 kB, Toke aHoga 2 A) Anode current at zero grid voltage, A:
voltage [1]	1.5 kV	Hyneson Tok aHoga, A: atanode voltage 1.5kV 2.4-36
voltage [2]	2.4 kV	Hyneson Tok aHoga, A: atanode voltage 1.5kV 2.4-36
voltage [3]	-36 kV	Hyneson Tok aHoga, A: atanode voltage 1.5kV 2.4-36
voltage [1]	15 kV	npuv HanpsxeHnv aHoga 1,5kB at peak anode voltage 3kV 6—10
voltage [2]	3 kV	npuv HanpsxeHnv aHoga 1,5kB at peak anode voltage 3kV 6—10
voltage [3]	6 kV	npuv HanpsxeHnv aHoga 1,5kB at peak anode voltage 3kV 6—10
voltage [4]	-10 kV	npuv HanpsxeHnv aHoga 1,5kB at peak anode voltage 3kV 6—10
voltage	4.5 kV	. .. Cutoff voltage (at anode voltage 4.5 kV,
current [1]	3 A	Hanpskenne 3anvpans (Npu Hanps>xeHun anode current 0.5 A), kV,atmost
current [2]	500 mA	Hanpskenne 3anvpans (Npu Hanps>xeHun anode current 0.5 A), kV,atmost
Interelectrode capacitance, pF [1]	45 pF	aHoga 4,5 kB, Toke aHoga 0,5 A), kB, He 6onee Interelectrode capacitance, pF:
Interelectrode capacitance, pF [2]	5 pF	aHoga 4,5 kB, Toke aHoga 0,5 A), kB, He 6onee Interelectrode capacitance, pF:
Interelectrode capacitance, pF [3]	6 pF	aHoga 4,5 kB, Toke aHoga 0,5 A), kB, He 6onee Interelectrode capacitance, pF:
input,atmost	6	MexanekTpoaHbte emxkocTu, Nd, He 6onee: input,atmost
voltage, absolute value, kV	1.5 kV	Hanps>keHne ceTkV oTpuyaTensHoe Nagative grid voltage, absolute value, kV 1.5
current, A [1]	3 A	(abconTHOE 3Ha4YeHue), kB 1,5 Filament startingcurrent, A
current, A [2]	15 A	(abconTHOE 3Ha4YeHue), kB 1,5 Filament startingcurrent, A
Dissipation, W	225 W	MyckoBor TOK HaKana, A 225 Dissipation, W:
anode [1]	1	PaccevsaeMas MowWwHOCTb, BT: anode ... 1- 10*

PARAMETER	PUBLISHED VALUE	CONDITION / NOTE
anode [2]	-10	Paccevsasma MowWwHOCTb, BT: anode ... 1-10*
grid [1]	10	AHOAOM .« oot 1,0-10* grid .. 300
grid [2]	-10	AHOAOM .« oot 1,0-10* grid .. 300
grid [3]	300	AHOAOM .« oot 1,0-10* grid .. 300
Temperature at stem and seals, °C [1]	300 C	CETKOM ..ottt e e e 300 Temperature at stem and seals, °C 150
Temperature at stem and seals, °C [2]	150 C	CETKOM ..ottt e e e 300 Temperature at stem and seals, °C 150
grid;) [1]	2	2 I LA V. anode-grid;)4 V b j/
grid;) [2]	4	2 I LA V. anode-grid;)4 V b j/